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(54) **SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

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A semiconductor device includes a substrate having an active region defined by an isolation layer, a word line crossing the active region and extending, within the substrate, in a first horizontal direction inside a word line trench, the word line trench being formed in the substrate and including a first sub word line trench and a second sub word line trench. A width, in the first horizontal direction, of a lower surface of the first sub word line trench is greater than a width, in the first horizontal direction, of a lower surface of the second sub word line trench, and a first distance between the lower surface of the first sub word line trench and an upper surface of the active region is less than a second distance between the lower surface of the second sub word line trench and the upper surface of the active region.

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